

## PRELIMINARY

### DESCRIPTION:

The DPZ2MS16P is a 32 megabit CMOS FLASH Electrically Erasable and Programmable nonvolatile memory module. The module is built with sixteen 256K x 8 FLASH memory devices and 2 high speed decoders. The DPZ2MS16P can be user configurable as 2048K x 16 or 4096K x 8 bits.

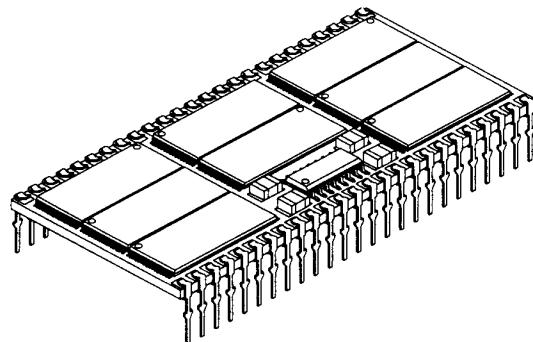
By utilizing TSOP packages and double sided surface mounting, the DPZ2MS16P is able to attain a density of over 10 Megabits per square inch of board space while maintaining a low profile (0.240" max.). The module is available with either through hole leads (DPZ2MS16P), or surface mount leads (DPZ2MS16XP).

Dense-Pac manufactures the DPZ2MS16XP with high temperature solder (232°C) on the components and (275°C) leads, allowing the module to be used with standard reflow/vapor phase surface mount soldering techniques, while maintaining complete mechanical integrity.

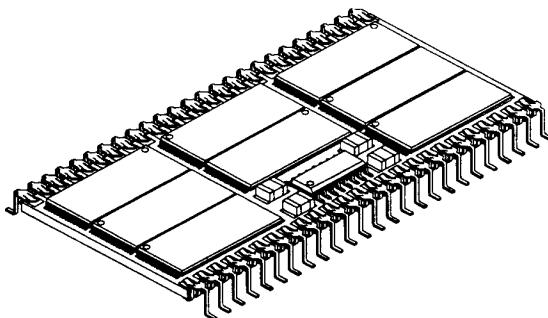
The DPZ2MS16P is ideal for use in systems that require periodic code updates, or for use as a high speed nonvolatile storage medium.

### FEATURES:

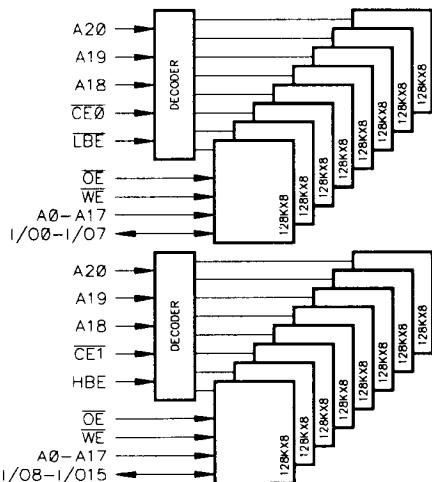
- Organization: 2048K x 16 or 4096K x 8
- Fast Read Access Times: 200, 250, 300ns
- Low Power:
  - 75mA Maximum Active (16 bit Mode)
  - 45mA Maximum Active (8 bit Mode)
  - 1.6 mA Maximum Standby
- 10,000 Erase/Program Cycles Minimum
- Command Register Architecture for Microprocessor Compatible Write Interface.
- 12.0V ±5% V<sub>PP</sub>
- TTL-Compatible Inputs and Outputs
- 50-Pin, 1.200 Ceramic DIP/Gullwing Packages
- 0.220" High (DPZ2MS16XP)/0.240" High (DPZ2MS16P)



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**FUNCTIONAL BLOCK DIAGRAM**



**PIN-OUT DIAGRAM**

VPP	1	A20
VDD	2	VSS
A11	3	OE
A9	4	A10
A8	5	I/O7
A13	6	I/O8
WE	7	I/O6
A19	8	I/O9
A18	9	I/O5
A17	10	I/O10
CE0	11	I/O11
LBE	12	I/O3
CE1	13	I/O4
HBE	14	I/O12
VDD	15	VSS
A15	16	I/O13
A16	17	I/O2
A14	18	I/O14
A12	19	I/O1
A7	20	I/O15
A6	21	I/O0
A5	22	A0
A4	23	A1
A3	24	A2
VDD	25	VSS

**FOR FURTHER INFORMATION  
SEE CHAPTER 9  
FOR COMPLETE DATA SHEET**